**Philips Semiconductors** 

**Product specification** 

# Rectifier diodes Schottky barrier

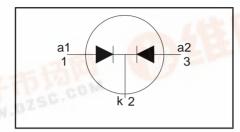
## PBYR7025WT series

#### **FEATURES**

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- · Low thermal resistance

#### **SYMBOL**

WWW.DZSC.



#### QUICK REFERENCE DATA

$$V_R = 20 \text{ V} / 25 \text{ V}$$
 $I_{O(AV)} = 70 \text{ A}$ 
 $V_F \le 0.46 \text{ V}$ 

#### **GENERAL DESCRIPTION**

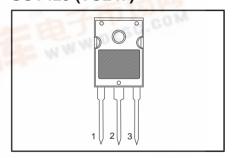
Dual, common cathode schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR7025WT series is supplied in the conventional leaded SOT429 (TO247) package.

#### **PINNING**

PIN	DESCRIPTION	
1	anode 1 (a)	
2	cathode (k)	
3	anode 2 (a)	
tab	cathode	
	l .	

# SOT429 (TO247)



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage	T <sub>mb</sub> ≤ 116 °C	H	- <b>20</b> 20 20 20	<b>-25</b> 25 25 25	V V V
I <sub>O(AV)</sub> I <sub>FRM</sub>	Average output current (both diodes conducting) Repetitive peak forward current per diode Non-repetitive peak forward	$T_{mb} \le 114 ^{\circ}\text{C}$  t = 10 ms	- -	70 70 50	0	A A A
	current, per diode	$\begin{array}{l} t = 8.3 \text{ ms} \\ \text{sinusoidal T}_i = 125 \text{ °C prior} \\ \text{to surge; with reapplied} \\ V_{\text{RRM(max)}} \\ t_p = 2  \mu\text{s}; \delta = 0.001 \end{array}$		55	ZSC.CO	A
RRM	Repetitive peak reverse current per diode	$l_p = 2 \mu S, \delta = 0.001$	14	. 101 ** 2	<u> </u>	A
I <sub>RSM</sub>	Non-repetitive peak reverse current per diode	t <sub>p</sub> = 100 μs	-	2	2	А
${\mathsf T}_{stg} \atop {\mathsf T}_{\mathsf j}$	Storage temperature Operating junction temperature	COM	-65 -	15 15	-	°C

### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>		per diode	-	-	0.9	K/W
	mounting base	both diodes	-	-	0.65	K/W
R <sub>th j-a</sub>		in free air	-	45	-	K/W
A DDE	ambient					

Rectifier diodes Schottky barrier PBYR7025WT series

# **ELECTRICAL CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	Forward voltage (per diode)	I <sub>F</sub> = 35 A; T <sub>j</sub> = 125°C I <sub>F</sub> = 70 A; T <sub>j</sub> = 125°C	-	0.40	0.46	<b>\</b>
		I <sub>F</sub> = 70 A; T <sub>i</sub> = 125°C	-	0.52	0.54	V
		$I_{\rm F} = 70  \text{A}$	-	0.58	0.64	V
I <sub>R</sub>	Reverse current (per diode)	$V_R = V_{RRM}$	-	0.8	15	mΑ
	, ,	$V_{R}^{N} = V_{RRM}^{NN}$ ; $T_{i} = 100  ^{\circ}C$	-	40	120	mΑ
C <sub>d</sub>	Junction capacitance (per	$V_R = V_{RRM}^{(NN)}$ ; $T_j = 100 ^{\circ}$ C $f = 1MHz$ ; $V_R = 5V$ ; $T_j = 25 ^{\circ}$ C to	-	2100	-	pF
	diode)	125 °C				

# Rectifier diodes Schottky barrier

#### PBYR7025WT series

**Product specification** 

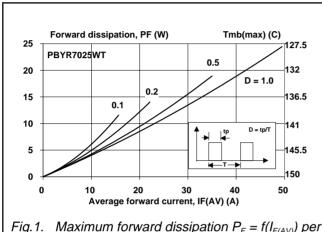
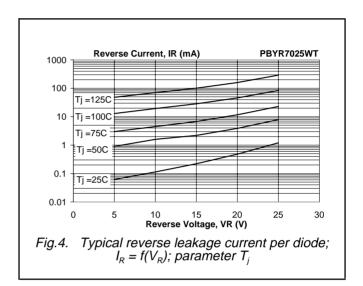


Fig.1. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; square current waveform where  $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$ .



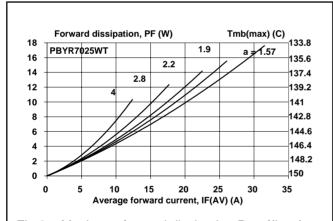


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; sinusoidal current waveform where  $a = f(I_{F(AV)})$  $factor = I_{F(RMS)} / I_{F(AV)}$ 

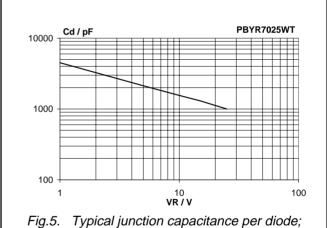


Fig.5. Typical junction capacitance per diode;  $C_d = f(V_R)$ ; f = 1 MHz;  $T_j = 25$ °C to 150 °C.

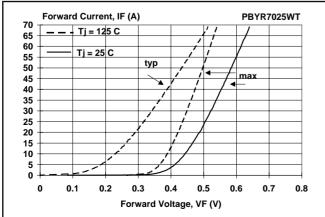
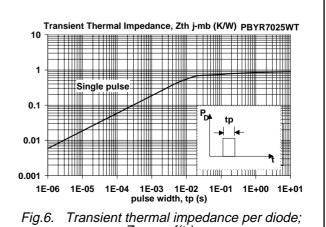


Fig.3. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter T

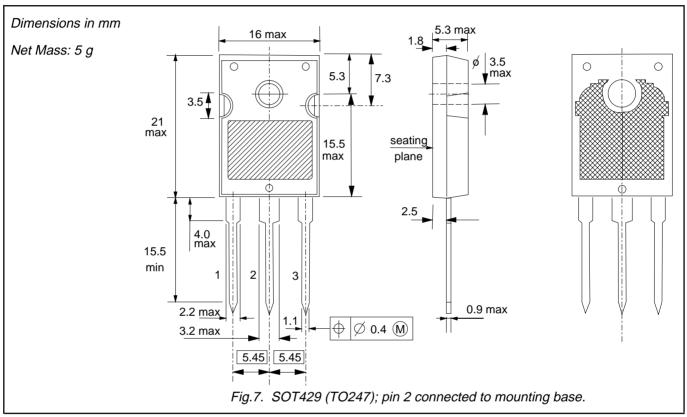


 $Z_{th\ j-mb} = f(t_p).$ 

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# PBYR7025WT series

#### **MECHANICAL DATA**



- Refer to mounting instructions for SOT429 envelope.
   Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier	diodes
Schottky	barrier

PBYR7025WT series

#### **DEFINITIONS**

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				

#### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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